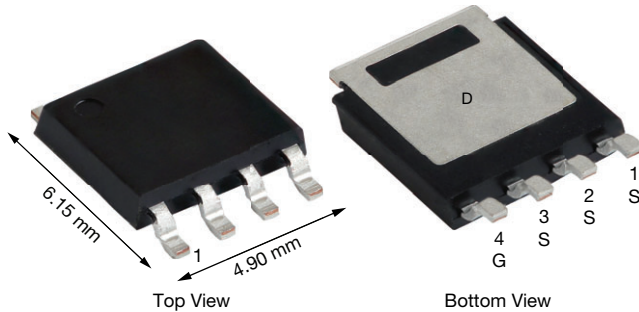




**THE DATASHEET OF
SQJ180EP-T1_GE3**

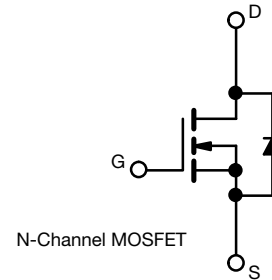


Automotive N-Channel 80 V (D-S) 175 °C MOSFET

PowerPAK® SO-8L

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE


RoHS
 COMPLIANT
 HALOGEN
FREE


PRODUCT SUMMARY	
V _{DS} (V)	80
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.0030
I _D (A)	248
Configuration	Single
Package	PowerPAK SO-8L

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	80	V
Gate-source voltage		V _{GS}	± 20	
Continuous drain current	T _C = 25 °C	I _D	248	A
	T _C = 125 °C		143	
Continuous source current (diode conduction)		I _S	248	
Pulsed drain current		I _{DM}	420	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	42	
Single pulse avalanche energy		E _{AS}	88	mJ
Maximum power dissipation	T _C = 25 °C	P _D	500	W
	T _C = 125 °C		166	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^b			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^a	R _{thJA}	42	°C/W
Junction-to-case (drain)		R _{thJC}	0.3	

Notes

- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



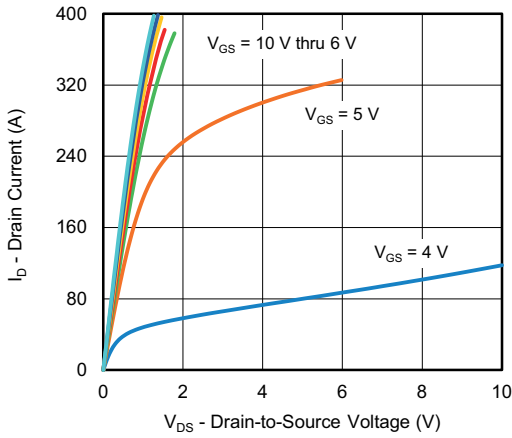
SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$	80	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.2	2.7	3.5	
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$	-	-	10	μA
		$V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	250	
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}, V_{DS} \geq 5\text{ V}$	30	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$	-	0.0025	0.0030	Ω
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.0059	
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.0075	
Forward transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$	-	82	-	S
Dynamic ^b						
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	4746	6645	μF
Output capacitance	C_{oss}		-	814	1140	
Reverse transfer capacitance	C_{rss}		-	51	72	
Total gate charge ^c	Q_g	$V_{GS} = 10\text{ V}, V_{DS} = 40\text{ V}, I_D = 10\text{ A}$	-	78	117	nC
Gate-source charge ^c	Q_{gs}		-	18	-	
Gate-drain charge ^c	Q_{gd}		-	16	-	
Gate resistance	R_g	$f = 1\text{ MHz}$	0.5	1.0	1.50	Ω
Turn-on delay time ^c	$t_{d(on)}$	$V_{DD} = 40\text{ V}, R_L = 4\text{ }\Omega, I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$	-	16	20	ns
Rise time ^c	t_r		-	10	15	
Turn-off delay time ^c	$t_{d(off)}$		-	39	50	
Fall time ^c	t_f		-	9	15	
Source-Drain Diode Ratings and Characteristics ^b						
Pulsed current ^a	I_{SM}		-	-	420	A
Forward voltage	V_{SD}	$I_F = 15\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.1	V
Body diode reverse recovery time	t_{rr}	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	50	65	ns
Body diode reverse recovery charge	Q_{rr}		-	71	95	nC
Reverse recovery fall time	t_a		-	28	44	ns
Reverse recovery rise time	t_b		-	22	38	
Body diode peak reverse recovery current	$I_{RM(REC)}$			-	2.4	3.6

Notes

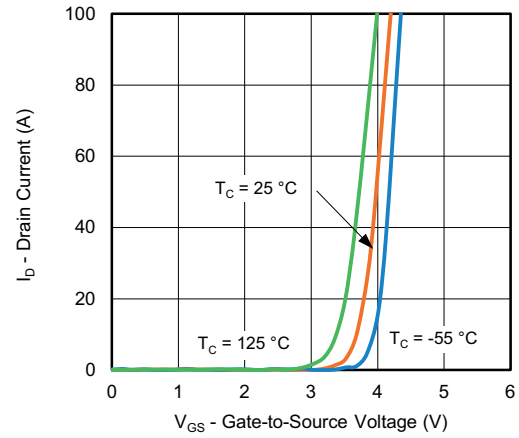
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

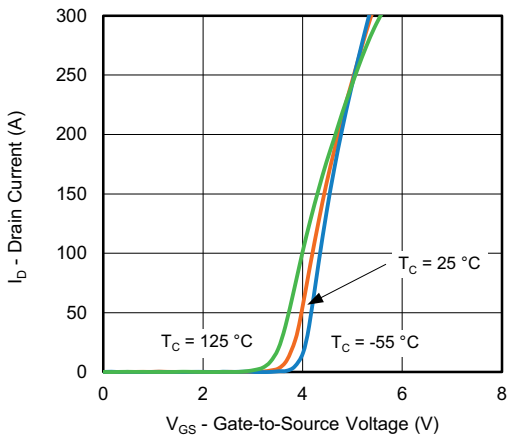
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



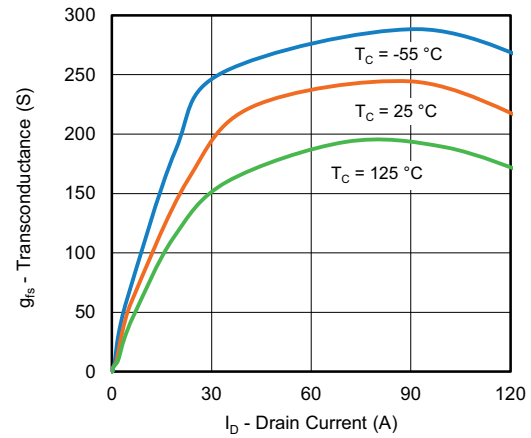
Output Characteristics



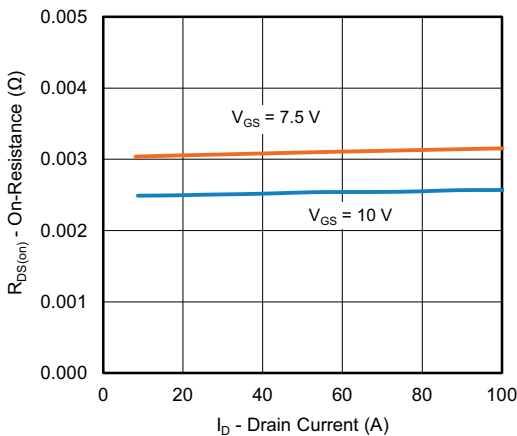
Transfer Characteristics



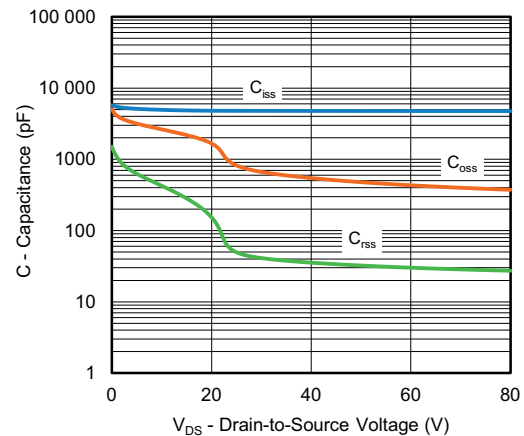
Transfer Characteristics



Transconductance



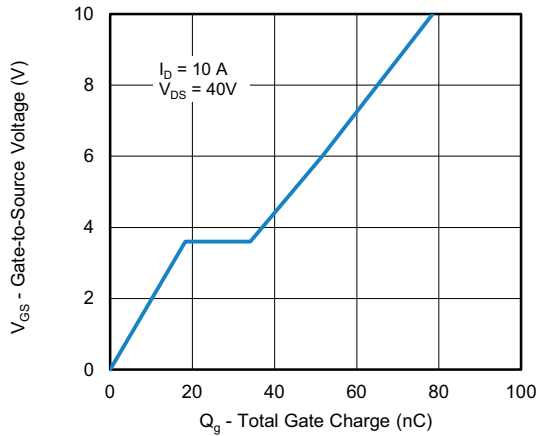
On-Resistance vs. Drain Current



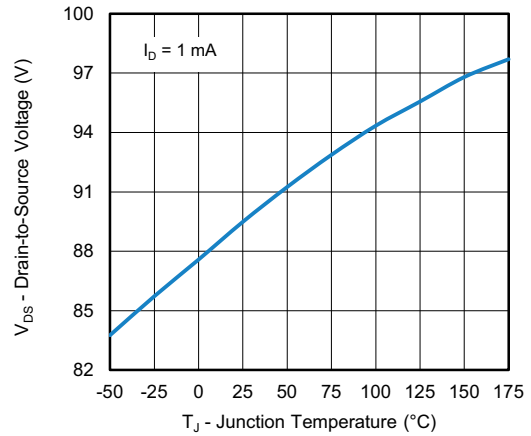
Capacitance



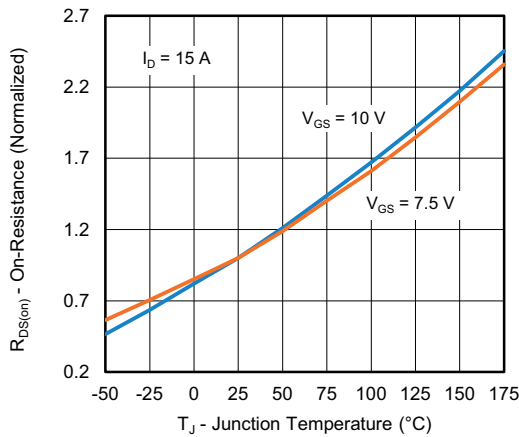
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



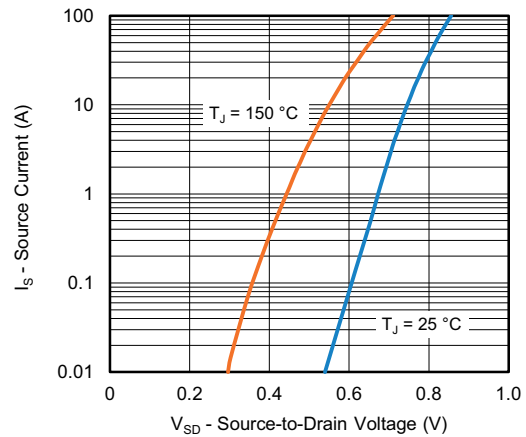
Gate Charge



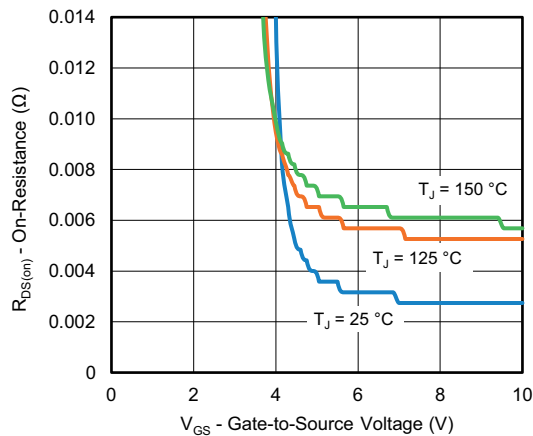
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Junction Temperature



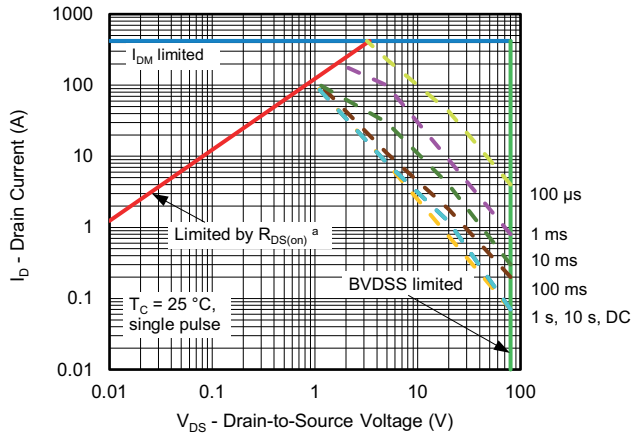
Source Drain Diode Forward Voltage



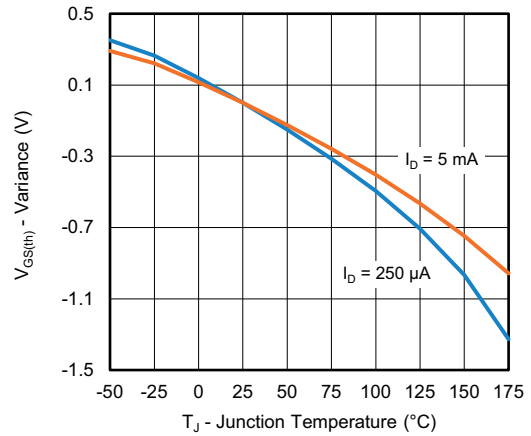
On-Resistance vs. Gate to Source Voltage



TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Safe Operating Area



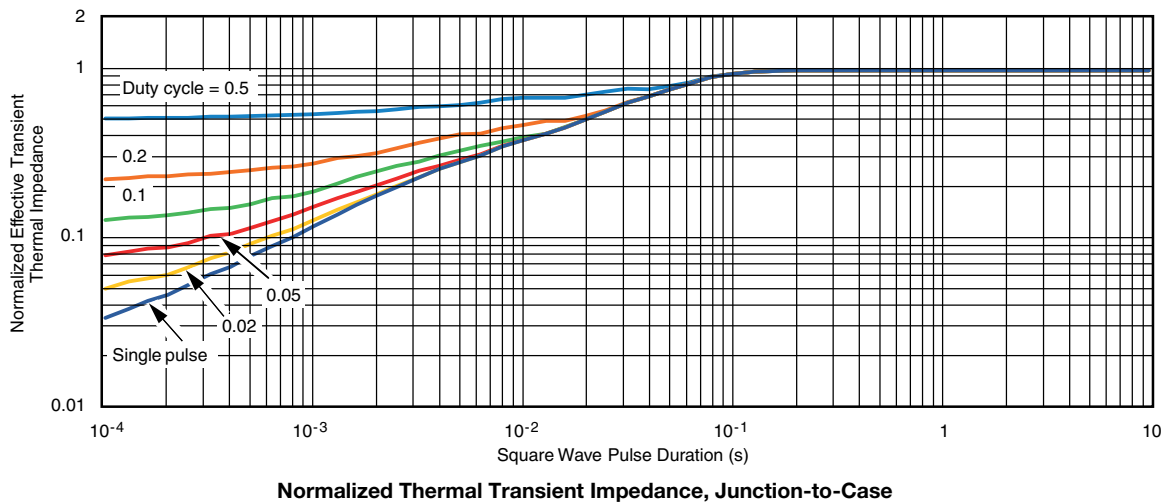
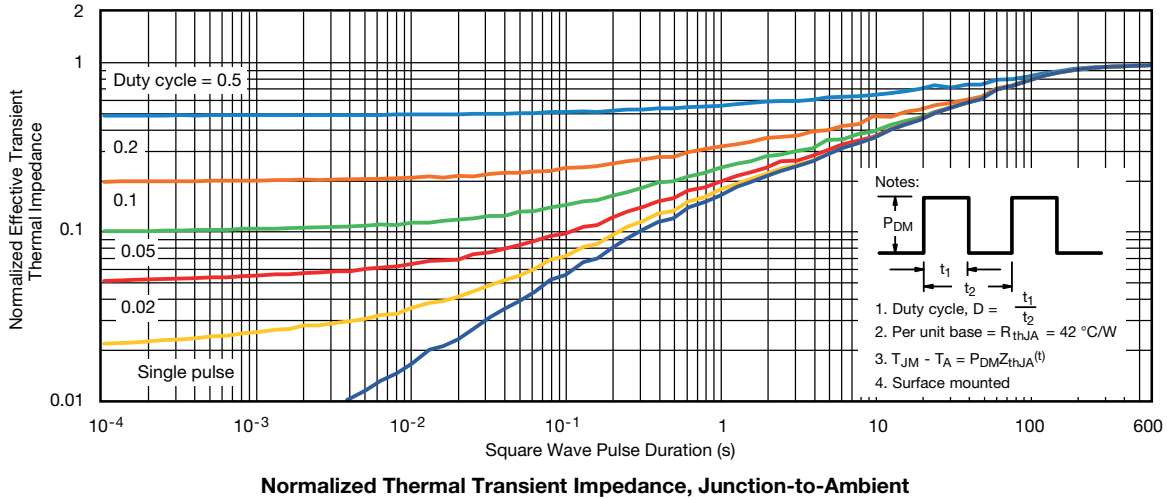
Threshold Voltage

Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



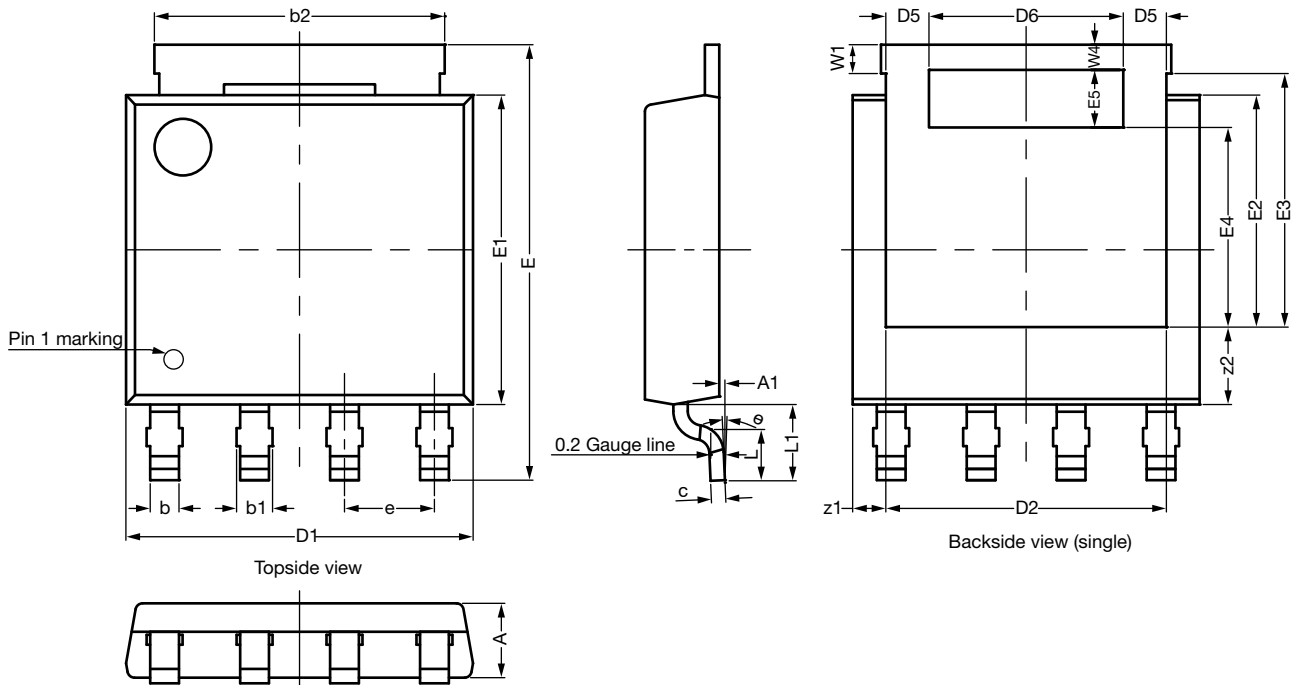
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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PowerPAK® SO-8L (PPKS08LWLA) Case Outline 3



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.05	1.10	0.039	0.041	0.043
A1	0.00	---	0.127	0.000	---	0.005
b	0.33	0.41	0.49	0.013	0.016	0.019
b1	0.43	0.51	0.59	0.017	0.020	0.023
b2	4.00	4.10	4.20	0.157	0.161	0.165
c	0.15	0.20	0.25	0.006	0.008	0.010
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D5	0.51	0.61	0.71	0.020	0.024	0.028
D6	2.64	2.74	2.84	0.104	0.108	0.112
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
E3	3.48	3.58	3.68	0.137	0.141	0.145
E4	2.72	2.82	2.92	0.107	0.111	0.115
E5	0.71	0.81	0.91	0.028	0.032	0.036
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
W1	0.31	0.41	0.51	0.012	0.016	0.020
W4	0.31	0.36	0.41	0.012	0.014	0.016
z1	0.37	0.47	0.57	0.015	0.019	0.022
z2	0.99	1.09	1.19	0.039	0.043	0.047
θ	0°	---	5°	0°	---	5°

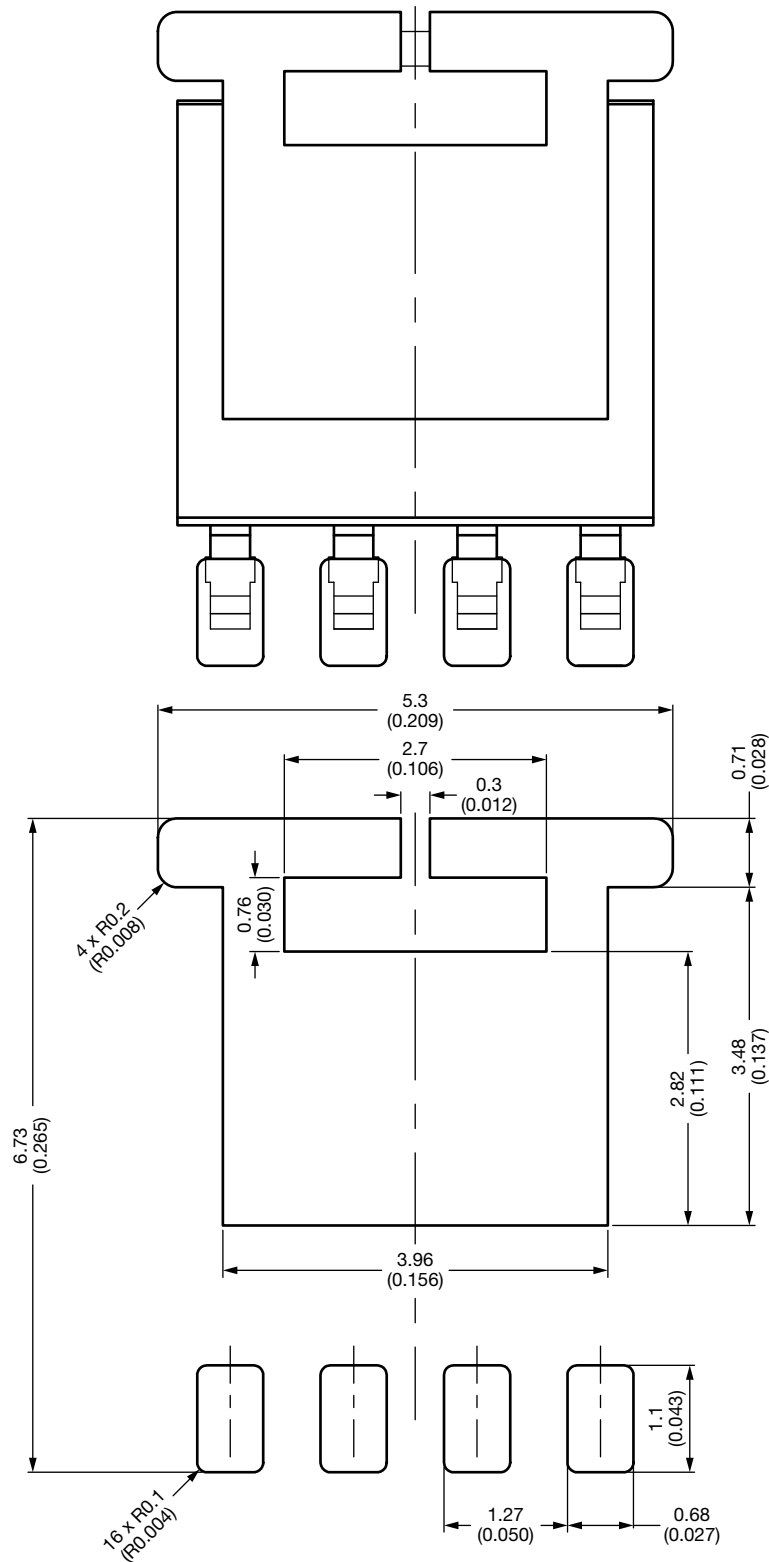
ECN: C23-1016-Rev. D, 18-Sep-2023
 DWG: 6067

Note

- Millimeter will govern



Recommended Land Pattern PowerPAK® SO-8L Single Short Ear





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